

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60V	5.0Ω@10V	0.34A
	5.3Ω@4.5V	

Feature

- ESD protection
- Advanced trench process technology
- High density cell design for ultra low on-resistance
- Very low leakage current in off condition
- In compliance with EU RoHS 2002/95/EC directives.
- Halogen-free

Application

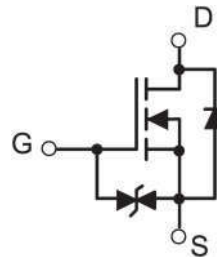
- Specially designed for battery operated system, solid-state relays drivers, relays, displays, lamps, solenoids, memories, etc.

Package

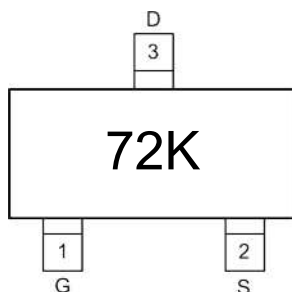


SOT-23

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	0.34	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

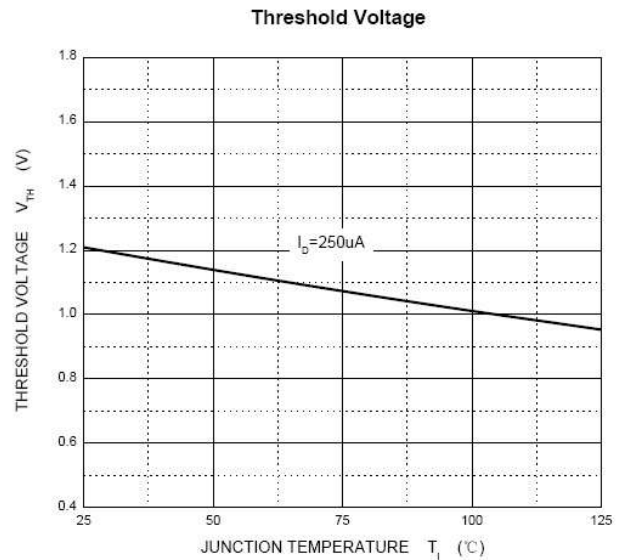
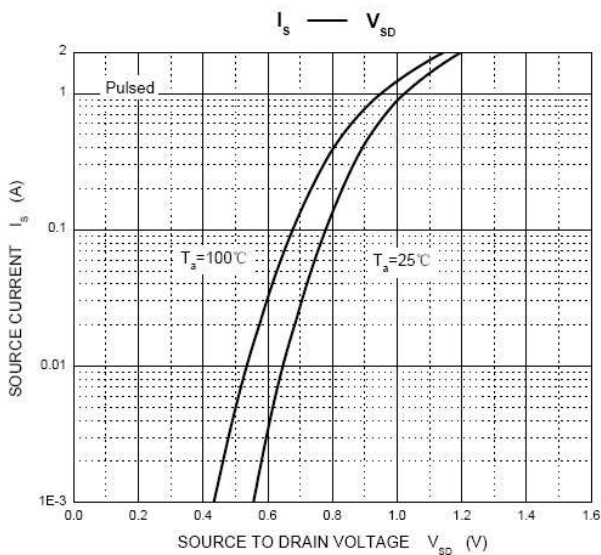
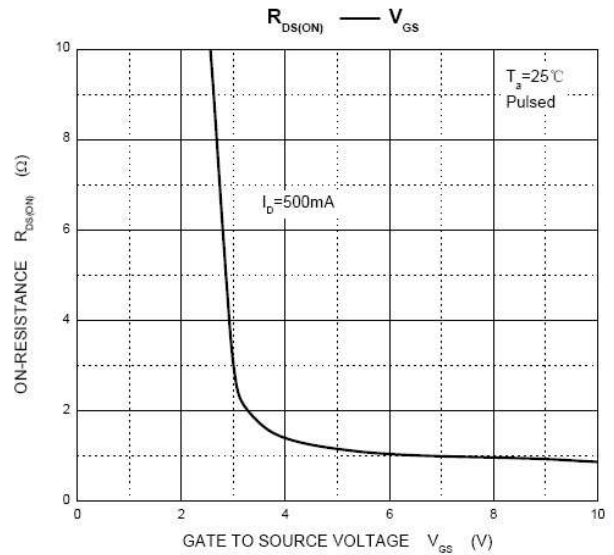
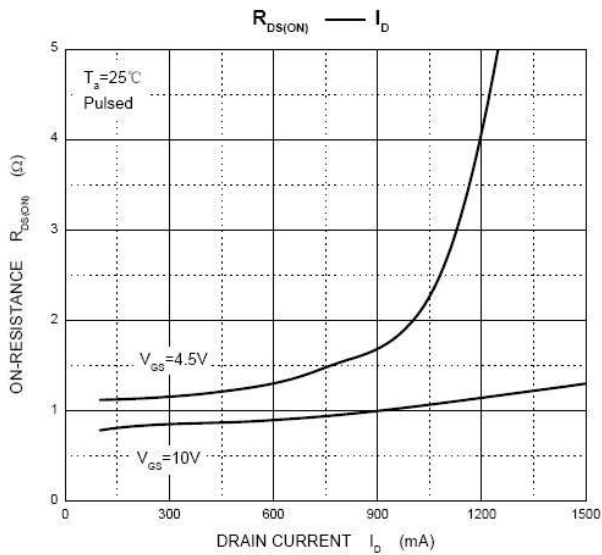
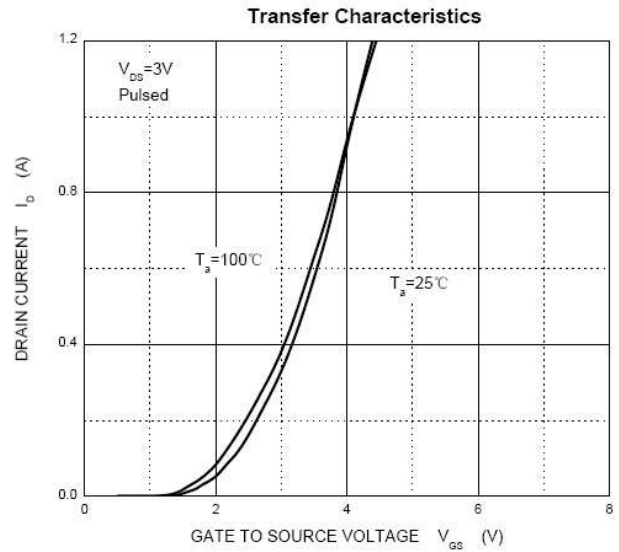
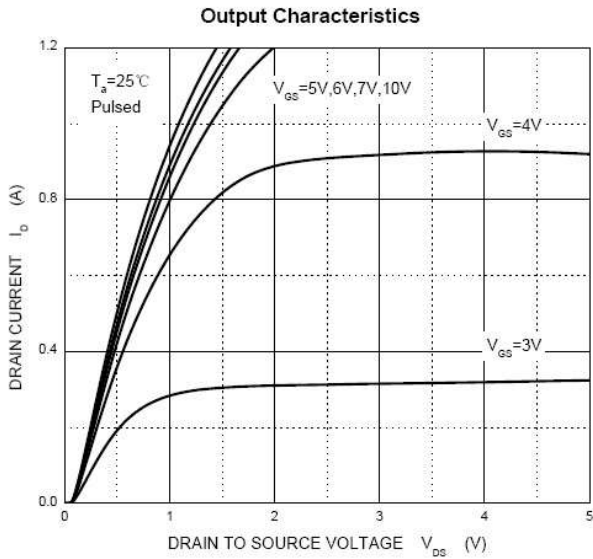
Electrical characteristics (TA=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS1}	$V_{GS} = \pm 20V, V_{DS} = 0V$			±10	μA
	I_{GSS2}	$V_{GS} = \pm 10V, V_{DS} = 0V$			±200	nA
	I_{GSS3}	$V_{GS} = \pm 5V, V_{DS} = 0V$			±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1.0		2.5	V
Drain-source on-resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$		1.0	5.0	Ω
		$V_{GS} = 4.5V, I_D = 0.2A$		1.1	5.3	
Dynamic characteristics²⁾						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	C_{oss}				30	
Reverse Transfer Capacitance	C_{rss}				10	
Recovered charge	Q_r	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu S$		30		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, R_L = 250\Omega, V_{GS} = 10V, R_{GS} = 50\Omega, R_G = 50\Omega$			10	nS
Turn-off delay time	$t_{d(off)}$				15	
Reverse recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, Dis/dt = -100a/uS$		30		nS
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	$V_{GS} = 0V, I_S = 0.3A$			1.5	V

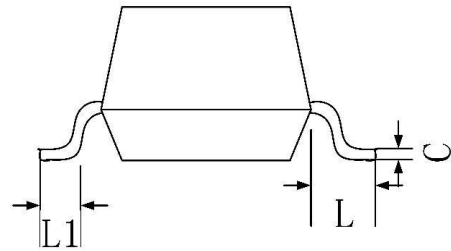
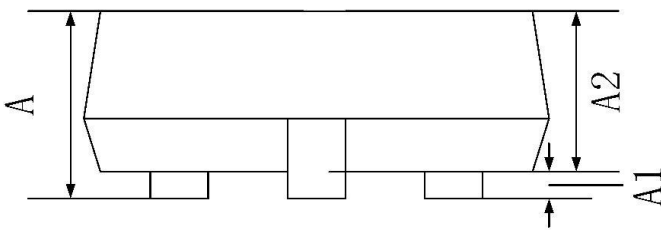
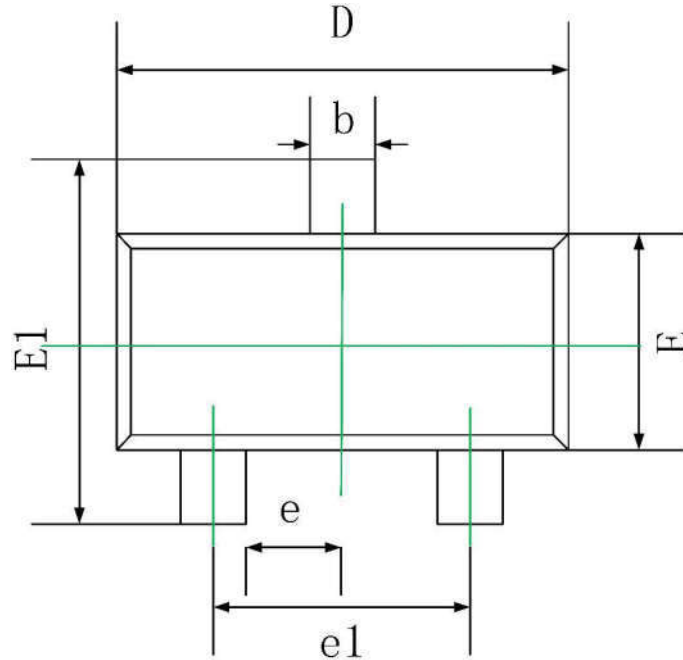
Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020